

Silicon PNP transistor epitaxial type

A5889

[Applications]

High speed switching

DC-DC convertor

Strobe flash

[Feature]

High DC gain hFE= 200-500 at VCE= -2V, IC= -0.5A

Low collector saturation voltage VCE(sat)= -0.19V (Max.) at IC= -1.6A, IB= -53mA

High speed switching time tf= 40ns (Typ.) at VCC= -12V, IC= -1.6A, IB= -53mA

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-20	V
Collector-emitter voltage	VCEO	-20	V
Emitter-base voltage	VEBO	-7	V
Collector current (DC)	IC	-3	A
Collector current (Pulse)	ICP	-5	A
Base current	IB	-0.3	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BVCEO	-20	-	-	V	IC= -10mA, IB= 0A
Collector cut-off current	ICBO	-	-	-100	nA	VCB= -20V, IE= 0A
Emitter cut-off current	IEBO	-	-	-100	nA	VEB= -7V, IC= 0A
DC current gain 1	hFE 1	200	-	500	-	VCE= -2V, IC= -0.5A
DC current gain 2	hFE 2	100	-	-	-	VCE= -2V, IC= -1.6A
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.19	V	IC= -1.6A, IB= -53mA
Base-emitter saturation voltage	VBE(sat)	-	-	-1.1	V	IC= -1.6A, IB= -53mA
Transition frequency	fT	-	160	-	MHz	VCE= -2V, IE= 0.5A
Collector output capacitance	Cob	-	40	-	pF	VCB= -10V, f = 1MHz, IE= 0A
Turn on time	ton	-	70	-	ns	VCC= -12V, IC= -1.6A -IB1= IB2= 53mA
Storage time	tstg	-	150	-	ns	
Fall time	tf	-	40	-	ns	

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

